

REMARKS/ARGUMENTS

Reconsideration of this application is requested. Claims 1-31 remain pending in the application of which claims 1-20 are directed to elected subject matter. Claims 21-31 remain pending in the application but have been withdrawn from consideration. These claims may be canceled upon the allowability of claims 1-20.

Claim 1 has been amended in order to more particularly point out and distinctly claim that which applicants regard as their invention and to direct it to preferred aspects of the description.

Claim 1 is amended to incorporate the features described in the original specification, especially in page 10, paragraph [0016] of the U.S. publication of the present application, which makes it clear a novel feature of present invention is that “a voltage applying process is performed simultaneously with an etching process”.

More specifically, as described in page 10, paragraphs [0015] to [0020], by simultaneously performing the etching process and the voltage applying process, one surface of the ferroelectric crystal is etched by dipping that surface in the etching solution and simultaneously a predetermined size of voltage is applied between the one surface and another surface of the ferroelectric crystal.

As the etching progresses during the etching process, the thickness of the ferroelectric crystal reduces and comes closer to the desired thickness d . When the thickness of the ferroelectric crystal reaches the desired thickness d , the polarization direction of the ferroelectric crystal is reversed, which greatly reduces the etching rate of the one surface. If the etching rate of the one surface is greatly reduced, the progress of the etching is substantially stopped. As a result, a ferroelectric crystal of the uniform desired thickness d can be obtained.

The cited reference Eason (US 6,344,150) does not disclose this novel feature of claim 1 in which “a voltage applying process is performed simultaneously with an etching process”. Eason only discloses a method in which “the etching process involves a controlled inversion or an alignment of ferroelectric domains in the substrate (e.g. through an electric poling process), *followed by* an etching of structural depressions which follows the domain-alignment boundaries” (*see* column 2, lines 4 to 8 of Eason). More specifically, in Eason, the polling process which applies a pulsed high voltage electric field is performed in order to determine an

etching pattern before the etching process (*see* column 4, lines 15 to 33), and then the etching process is performed without the pulsed high voltage electric field being applied (*see* column 5, lines 3 to 14), which means that Eason does not disclose the aforementioned novel feature of claim 1 in which the voltage applying process is performed simultaneously with the etching process.

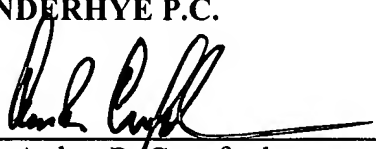
Applicants' claims as above amended define novel and inventive subject matter. The rejection in item 3 of the Official Action should be withdrawn as should the rejections in items 7 and 10. Claims 2-20 are dependent from claim 1 either directly or indirectly and are patentable as well because the limitations of an independent claim are incorporated into its dependent claims – MPEP §2143.03.

Reconsideration and favorable action are solicited.

Respectfully submitted,

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